

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14067	((257/79) or (257/8\$1) or (257/9\$1) or (257/100) or (257/101) or (257/102) or (257/103) or (372/43.01) or (372/108) or (385/125)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/15 20:23
L2	0	1 and photonic adj crystal.ti,ab, clm. and (guid\$3 wave-guid\$3 wave adj guid\$3) adj layer.ti,ab, clm. and (light-emitting light adj emitting).ti,ab,clm. and extract\$3. ti,ab,clm. and (hole aperture opening void).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 20:27
L3	0	1 and photonic adj crystal.ti,ab, clm. and (trap\$4 guid\$3 wave-guid\$3 wave adj guid\$3) adj layer.ti,ab,clm. and (light-emitting light adj emitting).ti,ab,clm. and extract\$3.ti,ab,clm. and (hole aperture opening void).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 20:27
L4	2	1 and photonic adj crystal.ti,ab, clm. and (trap\$4 guid\$3 wave-guid\$3 wave adj guid\$3) near4 layer.ti,ab,clm. and (light-emitting light adj emitting). ti,ab,clm. and extract\$3.ti,ab,clm. and (hole aperture opening void). ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 20:28
S2	148	(light-emitting light adj emitting laser semiconductor near2 optoelectronic).ti,ab,clm. and (transparent near4 electrode indium adj tin adj oxide ITO ZnO "ZnO.sub."S1 zinc adj oxide) and (photonic adj crystal extraction near10 grid radiative adj coupling near10 grid radiatively adj couple\$1 near6 grid)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 18:32
S3	66	(light-emitting light adj emitting laser semiconductor near2 optoelectronic).ti,ab,clm. and (transparent near4 electrode indium adj tin adj oxide ITO ZnO "ZnO.sub."S1 zinc adj oxide) and (photonic adj crystal extraction near10 grid radiative adj coupling near10 grid radiatively adj couple\$1 near6 grid)	USPAT	OR	ON	2005/07/21 16:08

S4	68	(light-emitting light adj emitting laser semiconductor near2 optoelectronic).ti,ab,clm. and (transparent near4 electrode indium adj tin adj oxide ITO ZnO "ZnO.sub."S1 zinc adj oxide) and (photonic adj crystal (extraction near10 (grating grid)) (radiative adj coupling near10 (grating grid)) (radiatively adj couple\$1 near6 (grating grid)))	USPAT	OR	ON	2005/07/21 16:10
S5	0	(light-emitting light adj emitting laser semiconductor near2 optoelectronic).ti,ab,clm. and (transparent near4 electrode indium adj tin adj oxide ITO ZnO "ZnO.sub."S1 zinc adj oxide) and (photonic adj crystal (extraction near10 (grating grid)) (radiative adj coupling near10 (grating grid)) (radiatively adj couple\$1 near6 (grating grid))) and ((guide guiding wave-guide) adj layer)	USPAT	OR	ON	2005/07/21 16:11
S6	0	(light-emitting light adj emitting laser semiconductor near2 optoelectronic).ti,ab,clm. and (transparent near4 electrode indium adj tin adj oxide ITO ZnO "ZnO.sub."S1 zinc adj oxide) and (photonic adj crystal (extraction near10 (grating grid)) (radiative adj coupling near10 (grating grid)) (radiatively adj couple\$1 near6 (grating grid))) and guide adj layer	USPAT	OR	ON	2005/07/21 16:11
S7	0	(light-emitting light adj emitting laser semiconductor near2 optoelectronic).ti,ab,clm. and (transparent near4 electrode indium adj tin adj oxide ITO ZnO "ZnO.sub."S1 zinc adj oxide) and (photonic adj crystal (extraction near10 (grating grid)) (radiative adj coupling near10 (grating grid)) (radiatively adj couple\$1 near6 (grating grid))) and waveguide adj layer	USPAT	OR	ON	2005/07/21 16:12

S8	68	(light-emitting light adj emitting laser semiconductor near2 optoelectronic).ti,ab,clm. and (transparent near4 electrode indium adj tin adj oxide ITO ZnO "ZnO.sub."S1 zinc adj oxide) and (photonic adj crystal (extraction near10 (grating grid)) (radiative adj coupling near10 (grating grid)) (radiatively adj couple\$1 near6 (grating grid)))	USPAT	OR	ON	2005/07/21 16:17
S9	0	(light-emitting light adj emitting laser semiconductor near2 optoelectronic).ti,ab,clm. and (transparent near4 electrode indium adj tin adj oxide ITO ZnO "ZnO.sub."S1 zinc adj oxide) and (photonic adj crystal (extraction near10 (grating grid)) (radiative adj coupling near10 (grating grid)) (radiatively adj couple\$1 near6 (grating grid))) and guiding adj layer	USPAT	OR	ON	2005/07/21 16:19
S10	3	(light-emitting light adj emitting laser semiconductor near2 optoelectronic).ti,ab,clm. and (photonic adj crystal (extraction near10 (grating grid)) (radiative adj coupling near10 (grating grid)) (radiatively adj couple\$1 near6 (grating grid))) and guiding adj layer	USPAT	OR	ON	2005/07/21 16:22
S11	0	(light-emitting light adj emitting laser semiconductor near2 optoelectronic).ti,ab,clm. and (photonic adj crystal) and waveguide adj layer and extraction near4 efficiency	USPAT	OR	ON	2005/07/21 16:23
S12	2	(light-emitting light adj emitting laser semiconductor near2 optoelectronic).ti,ab,clm. and (photonic adj crystal) and waveguide adj layer and extraction near4 efficiency	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 16:25
S13	2	(light-emitting light adj emitting laser semiconductor near2 optoelectronic).ti,ab,clm. and (photonic adj crystal extraction near3 (grid grating)) and waveguide adj layer and extraction near4 efficiency	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 16:26

S14	2	(light-emitting light adj emitting laser semiconductor near2 optoelectronic).ti,ab,clm. and (photonic adj crystal grid grating) and waveguide adj layer and extraction near4 efficiency	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 16:26
S15	8	(light-emitting light adj emitting laser semiconductor near2 optoelectronic).ti,ab,clm. and (photonic adj crystal grid grating) and waveguide adj layer and extraction near4 efficiency	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 17:02
S16	5	((("5,008,718") or ("5,779,924") or ("5,955,749") or ("6,323,063") or ("6,580,096"))).PN.	USPAT	OR	OFF	2005/07/21 17:04
S17	0	(U52003/0141507).CCLS.	USPAT	OR	OFF	2005/07/21 17:04
S18	0	("20030141507").PN.	USPAT	OR	OFF	2005/07/21 17:04
S19	1	("20030141507").PN.	US-PGPUB; USPAT	OR	OFF	2005/07/21 17:04
S20	723215	(light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 07:32
S21	3133	photonic adj crystal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 07:32
S22	267613	(ito indium-tin-oxide indium adj tin adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 07:45
S23	16879	waveguide adj (film layer) guide adj (layer film) guiding adj (layer film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 08:02
S24	7804	extraction near3 efficiency	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 07:34
S25	9332	(extracting extraction extract) near3 efficiency	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 07:35

S26	991707	S20 S21 S22 S23 S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 07:35
S27	1	S20 and S21 and S22 and S23 and S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 08:04
S28	389658	(ito indium-tin-oxide indium adj tin adj oxide zinc adj oxide zno "zno. sub."\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 07:46
S29	1	S20 and S21 and S28 and S23 and S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 07:52
S30	5	((("5977566") or ("6420732")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/22 07:52
S31	10010	(grin-sch sch separate adj confinement adj heterostructure graded adj refractive adj index adj separate adj confinement)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 08:03
S32	0	S20 and S21 and S22 and S31 and S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 08:04
S33	0	S20 and S21 and S28 and S31 and S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 08:09
S34	12	photonic adj crystal and (ito indium adj tin adj oxide indium-tin-oxide) and extraction near4 (efficiency efficiently efficient)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 09:54
S35	0	"6420732".ap. and transparent adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 09:54

S36	0	"6420732".ap. and transparent near6 oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 09:55
S37	0	"6420732".ap. and transparent and oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 09:55
S38	0	"6420732".ap. and transparent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 09:55
S39	0	"6420732".ap. and diodes	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 09:56
S40	2	("6420732").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/22 09:56
S41	1	S40 and transparent and oxide and ito	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/22 11:12
S42	1523	ITO near4 (thick thickness) and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 11:13
S43	863	ITO near4 (thick thickness) near4 nm and (light-emitting light adj emitting laser optoelectronic).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 11:13
S44	0	transparent near10 current adj spreading near10 ITO near4 (thick thickness) near4 nm and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 11:13
S45	290	transparent near10 ITO near4 (thick thickness) near4 nm and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 11:13

S46	1	transparent near10 ITO near4 (thick thickness) near4 nm and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm. and photonic adj crystal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 11:14
S47	1	transparent near10 ITO near4 (thick thickness) near4 nm and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm. and (optical photonic) adj crystal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 11:14
S48	8	ITO near4 (thick thickness) near4 nm and (light-emitting light adj emitting laser optoelectronic).ti, ab,clm. and (optical photonic) adj crystal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 11:51
S49	6	ITO near4 (thick thickness) near4 nm near10 wavelength and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:02
S50	7	(transparent near2 electrode ITO ZnO "ZnO.sub."\$1 zinc adj oxide) near4 (thick thickness) near4 nm near10 wavelength and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:48
S51	6	(electrode) near4 (thick thickness) near4 nm near10 wavelength and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:52
S52	6	(electrode) near4 (thick thickness) near4 ("ANG." nm) near10 wavelength and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:52
S53	6	(electrode) near4 (thick thickness) near4 ("ANG." nm Angstrom Angstrom) near10 wavelength and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:53
S54	7	(electrode) near4 (thick thickness) near4 ("ANG." nm Angstrom Angstrom ".mum.m" micron) near10 wavelength and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:54
S55	0	(electrode) near4 (thick thickness) near4 ("lambda."\$4 near10 wavelength) and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:56

S56	0	(electrode) near4 (thick thickness) near4 ("lambda."\$5 near10 wavelength) and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:56
S57	0	(electrode) near4 (thick thickness) near4 ("lambda."\$5) and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:57
S58	0	(electrode conductive adj layer) near4 (thick thickness) near4 ("lambda."\$5) and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:57
S59	0	(electrode conductive adj (film layer)) near4 (thick thickness) near4 ("lambda."\$5) and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:57
S60	0	(electrode conductive adj (film layer) transparent) near4 (thick thickness) near4 ("lambda."\$5) and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:57
S61	0	(electrode conductive adj (film layer) transparent) near4 ("lambda."\$5) and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:58
S62	0	(electrode conductive adj (film layer) transparent) near4 ("l."\$5) and (light-emitting light adj emitting laser optoelectronic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 12:58
S63	19	(US-20030020399-\$ or US-20030057417-\$ or US-20030141507-\$ or US-20030209714-\$ or US-20040150979-\$ or US-20040188689-\$ or US-20050035354-\$ or US-20050035362-\$).did. or (US-5008718-\$ or US-5463705-\$ or US-5779924-\$ or US-5955749-\$ or US-5970081-\$ or US-6323063-\$ or US-6580096-\$ or US-6630684-\$ or US-6803603-\$ or US-6420732-\$).did. or (US-20030057417-\$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/07/22 13:48

S64	0	("19andhexagonal").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/22 13:49
S65	6	S63 and hexagonal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/22 15:13
S66	230	photonic adj crystal near10 (electrode grid grating)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/22 15:31
S67	1091	photonic adj crystal.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/22 15:31
S68	70	photonic adj crystal.ti.	USPAT	OR	OFF	2005/07/22 15:31
S69	20	(US-20030020399-\$ or US-20030057417-\$ or US-20030141507-\$ or US-20030209714-\$ or US-20040150979-\$ or US-20040188689-\$ or US-20050035354-\$ or US-20050035362-\$ or US-20030209716-\$).did. or (US-5008718-\$ or US-5463705-\$ or US-5779924-\$ or US-5955749-\$ or US-5970081-\$ or US-6323063-\$ or US-6580096-\$ or US-6630684-\$ or US-6803603-\$ or US-6420732-\$).did. or (US-20030057417-\$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/07/22 16:06
S70	3	S69 and array near4 (laser led light-emitting light adj emitting)	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/07/22 16:06
S71	188	(thick thickness) near20 electrode near20 (frequency wavelength near20 (refracti\$2 near2 index)) and (light-emitting light adj emitting laser optoelectronic).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 13:02
S72	2	jp-07240277\$-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 13:31

S73	64689	(metal gold current adj spreading alumin\$um silver) near10 (ITO transparent ZnO "ZnO.sub."\$2 indium-tin-oxide indium adj oxide adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 13:32
S74	9342	(metal gold current adj spreading alumin\$um silver) near10 (ITO transparent ZnO "ZnO.sub."\$2 indium-tin-oxide indium adj oxide adj oxide) and (light-emitting light adj emitting laser optoelectronic). ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 13:32
S75	5693	(metal gold current adj spreading alumin\$um silver) near4 (ITO transparent ZnO "ZnO.sub."\$2 indium-tin-oxide indium adj oxide adj oxide) and (light-emitting light adj emitting laser optoelectronic). ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 13:33
S76	78	(current adj spreading) near4 (ITO transparent ZnO "ZnO.sub."\$2 indium-tin-oxide indium adj oxide adj oxide) and (light-emitting light adj emitting laser optoelectronic). ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 13:56
S77	2873	lindner.in.	EPO; DERWENT	OR	ON	2005/07/23 13:44
S78	0	lindner.in. and ito	EPO; DERWENT	OR	ON	2005/07/23 13:44
S79	67	lindner.in. and electrode	EPO; DERWENT	OR	ON	2005/07/23 13:46
S80	4	"239766".ap.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 13:54
S81	0	wo-0171334\$-\$\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 13:54
S82	1	wo-200171334\$-\$\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 13:54

S83	0	wo-2001071334\$-\$\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 13:55
S84	0	wo-01071334\$-\$\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 13:55
S85	14	(current adj spreading) near4 (ITO) and (light-emitting light adj emitting laser optoelectronic).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 14:10
S86	36	(NiAu "Ni/Au" "Au/Ni") near10 ITO and (light-emitting light adj emitting laser optoelectronic).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 14:57
S87	3	plurality near2 (light-emitting light adj emitting laser).ti,ab,clm. and (mesh-like grid) near6 electrode near4 transparent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 15:46
S88	11	ep-138177\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 15:47
S89	9	"6495862"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 15:47
S90	2	("6495862").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/23 15:48
S91	0	wo-01091194\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/23 15:48
S92	0	wo-2001091194\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/23 15:48

S93	1	wo-200191194\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/23 15:48
S94	8270	((257/79) or (257/8\$1) or (257/9\$1) or (257/100) or (257/101) or (257/102) or (257/103) or (372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50) or (372/108) or (385/125)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/07/23 17:11
S95	1716	S94 AND (EXTRACTION EFFICIENCY) AND (GRID GRATING PHOTONIC WAVEGUIDE GUIDE GUIDING)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/23 16:30
S96	1276	S94 AND (EXTRACTION EFFICIENCY) AND (GRID GRATING PHOTONIC WAVEGUIDE GUIDE GUIDING) AND (LIGHT-EMITTING LIGHT ADJ EMITTING LASER).TI,AB,CLM.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/23 16:31
S97	23	(US-20050151145-\$ or US-20050087754-\$ or US-20050035362-\$ or US-20050035354-\$ or US-20040188689-\$ or US-20030209716-\$ or US-20030209714-\$ or US-20030160259-\$ or US-20030141507-\$ or US-20030075714-\$ or US-20030071564-\$ or US-20030059185-\$).did. or (US-6831302-\$ or US-6803603-\$ or US-6788862-\$ or US-6630684-\$ or US-6586775-\$ or US-6420732-\$ or US-5955749-\$ or US-5619521-\$ or US-5008718-\$ or US-4879250-\$ or US-3806777-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/07/23 16:54
S98	15	flip-chip and (light-emitting light adj emitting).ti,ab,clm. and substrate and active and (photonic adj crystal grid near2 electrode grating near2 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/23 17:13

S99	24	substrate near6 (separat\$3 guid\$3 adj (region layer film)) and (light-emitting light adj emitting). ti,ab,clm. and substrate and active and (photonic adj crystal grid near2 electrode grating near2 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/23 17:14
S100	5	"773943".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 19:32
S101	1	(US-20050173717-\$).did.	US-PGPUB	OR	OFF	2006/01/14 19:37
S102	1	(US-20050173717-\$).did.	US-PGPUB	OR	OFF	2006/01/14 20:14
S103	1	S100 and photonic adj crystal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 20:25
S104	2	("6868107").PN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/14 20:25
S105	0	("jp-20050094956\$-\$).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/14 20:28
S106	2	"20050094956".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/14 20:29
S107	2	"20030113067".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/14 20:30
S108	4	S106 S107	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/14 20:30
S109	32	"5970081"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/14 20:47

S11 0	2	"5970081".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/14 21:44
S11 1	93	photonic adj crystal and light-emitting adj (diode element diode) and (waveguide wave adj guide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 00:15
S11 2	3	("6803603").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/14 22:30
S11 3	1	S112 and (wave adj guide waveguide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/14 22:30
S11 4	47	photonic adj crystal and light-emitting adj (diode element diode) and (waveguide wave adj guide)	USPAT	OR	ON	2006/01/15 00:23
S11 5	6	extraction near6 (photonic adj crystal) and light adj emitting.ti, ab,clm.	USPAT	OR	ON	2006/01/15 00:24
S11 6	4	extraction near6 (photonic adj crystal) and light adj emitting.ti, ab,clm. and (wave adj guide waveguide)	USPAT	OR	ON	2006/01/15 00:31
S11 7	0	extraction near6 (photonic adj crystal).ti,ab,clm. and light adj emitting.ti,ab,clm. and (wave adj guide waveguide)	USPAT	OR	ON	2006/01/15 00:26
S11 8	3	extraction near6 (photonic adj crystal) and light adj emitting.ti, ab,clm. and (wave adj guide waveguide) and (light adj emitting active) adj layer	USPAT	OR	ON	2006/01/15 00:32
S11 9	23	photonic adj crystal and light-emitting adj (diode element device) and ito near3 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 09:54
S12 0	0	photonic adj crystal near10 (hole aperture opening) near10 electrode and light-emitting adj (diode element device)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 09:55

S12 1	2	photonic adj crystal near10 (hole aperture opening) near10 electrode and (laser light-emitting adj (diode element device))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 09:57
S12 2	2	("5995749").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/15 09:57
S12 3	54	(US-20010000943-\$ or US-20030020399-\$ or US-20030044639-\$ or US-20030057417-\$ or US-20030059185-\$ or US-20030071564-\$ or US-20030075714-\$ or US-20030113067-\$ or US-20030141507-\$ or US-20030160259-\$ or US-20030209714-\$ or US-20030209716-\$ or US-20040150979-\$ or US-20040166362-\$ or US-20040188689-\$ or US-20040208466-\$ or US-20040227151-\$ or US-20050035354-\$ or US-20050035362-\$ or US-20050087754-\$ or US-20050094956-\$ or US-20050116625-\$ or US-20050151145-\$ or US-20050173717-\$ or US-20050226294-\$ or US-20050271092-\$).did. or (US-20050285128-\$).did. or (US-3806777-\$ or US-4879250-\$ or US-5008718-\$ or US-5463705-\$ or US-5619521-\$ or US-5779924-\$ or US-5955749-\$ or US-5970081-\$ or US-6323063-\$ or US-6420732-\$ or US-6495862-\$ or US-6574383-\$ or US-6580096-\$ or US-6586775-\$ or US-6630684-\$ or US-6788862-\$ or US-6803603-\$ or US-6831302-\$ or US-6847056-\$ or US-6868107-\$ or US-6958494-\$ or US-6967437-\$).did. or (JP-07240277-\$).did. or (US-20030057417-\$ or US-20030113067-\$ or US-20030231689-\$ or US-20050094956-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2006/01/15 09:57

S12 4	0	("Sandjoannopoulos.in.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/15 09:58
S12 5	2	S123 and joannopoulos.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 09:59
S12 6	0	S125 and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 10:08
S12 7	0	erchak.in. and electrode near4 (hole aperture opening)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 10:08
S12 8	0	erchak.in. and electrode near4 (pattern patterned patterning hole aperture opening)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 10:10
S12 9	176	photonic adj crystal and electrode near4 (pattern patterned patterning hole aperture opening)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 10:10
S13 0	60	photonic adj crystal.ti,ab,clm. and electrode near4 (pattern patterned patterning hole aperture opening)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 10:10
S13 1	39	photonic adj crystal.ti,ab,clm. and electrode near4 (hole aperture opening)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 11:27
S13 2	486	photonic adj crystal near6 (hole opening aperture)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 11:28
S13 3	0	(photonic adj crystal near6 (hole opening aperture)); near20 (electrode near6 (pattern patterned patterning))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 11:29

S13 4	3	(photonic adj crystal near6 (hole opening aperture)) near20 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 11:32
S13 5	2	("6674778").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/15 11:33
S13 6	1	S135 and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 11:53
S13 7	69	dbr and light-emitting adj diode and (single adj mode "few" adj mode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 11:54
S13 8	8	dbr near6 (single adj mode "few" adj mode) and light-emitting adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 11:56
S13 9	8	dbr near6 (single adj mode "few" adj mode) and light-emitting adj diode and (hole aperture opening)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 11:56
S14 0	0	dbr near6 (single adj mode "few" adj mode) and light-emitting adj diode and (hole aperture opening) and photonic adj crystal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 11:56
S14 1	8	dbr near6 (single adj mode "few" adj mode) and light-emitting adj diode and (hole aperture opening)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 12:08
S14 2	8	dbr near6 (single adj mode "few" adj mode) and light-emitting adj diode and vCSEL	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 12:29
S14 3	26	dbr near6 (single adj mode "few" adj mode) and vCSEL	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 12:54

S14 4	0	"200400131157".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 12:54
S14 5	2	"20040013157".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 12:54
S14 6	35	dbr and (guide guiding waveguide wave adj guide) and (light-emitting light adj emitting) and photonic adj crystal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 17:54
S14 7	5	dbr and (guide guiding waveguide wave adj guide) and (light-emitting light adj emitting) and photonic adj crystal and electrode near6 (hole aperture opening)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 18:02
S14 8	4	(guide guiding waveguide wave adj guide) near3 (active adj layer) and (light-emitting light adj emitting) and photonic adj crystal and electrode near6 (hole aperture opening)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 18:03
S14 9	24	(guide guiding waveguide wave adj guide) near3 (active adj layer) and (light-emitting light adj emitting) and vertical\$2 near3 emission	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 18:04
S15 0	13	(guide guiding waveguide wave adj guide) near3 (active adj layer) and (light-emitting light adj emitting).ti,ab,clm. and vertical\$2 near3 emission	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 18:05
S15 1	13	(guide guiding waveguide wave adj guide) near3 (active adj layer) and (light-emitting light adj emitting) adj (diode element device).ti,ab,clm. and vertical\$2 near3 emission	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 18:06
S15 2	8	(guide guiding waveguide wave adj guide) near3 (active adj layer) and (light-emitting light adj emitting) adj (diode element device).ti,ab,clm. and vertical\$2 near3 emission and guide adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 18:09

S15 3	11	(guide guiding waveguide wave adj guide) near3 (active adj layer) and (light-emitting light adj emitting) adj (diode element device) and vertical\$2 near3 emission and guide adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 18:10
S15 4	0	(guide guiding waveguide wave adj guide) near3 (active adj layer) and (light-emitting light adj emitting) adj (diode element device) same vertical\$2 near3 emission same guide adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 18:10
S15 5	288	(waveguide guide guiding wave-guide) near6 active adj (layer region) and (light-emitting light adj emitting).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 18:34
S15 6	1218	(waveguide guide guiding wave-guide) near6 (active adj (layer region)) and (light-emitting light adj emitting).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 18:35
S15 7	138	(waveguide guide guiding wave-guide) near6 (active adj (layer region)) and (light-emitting light adj emitting).ti,ab,clm. and vertical\$2 near4 (emission emitting emit)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 18:40
S15 8	2	(waveguide guide guiding wave-guide) near6 (active adj (layer region)) and (light-emitting light adj emitting).ti,ab,clm. and vertical\$2 near4 (emission emitting emit) and photonic adj crystal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 18:40
S15 9	28	(waveguide guide guiding wave-guide) near6 (active adj (layer region)) and (light-emitting light adj emitting).ti,ab,clm. and vertical\$2 near4 (emission emitting emit) and extract\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 18:55
S16 0	33	mqw near4 (guid guiding)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/15 20:21